Unit in mm

TOSHIBA TRANSISTOR SILICON NPN EPITAXIAL TYPE (PCT PROCESS)

2 S C 2 7 0 5

AUDIO FREQUENCY AMPLIFIER APPLICATIONS.

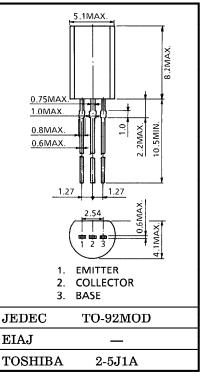
Complementary to 2SA1145.

Small Collector Output Capacitance : Coh = 1.8pF (Typ.)

: $f_T = 200 MHz$ (Typ.) High Transition Frequency

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CBO}	150	V
Collector-Emitter Voltage	v_{CEO}	150	V
Emitter-Base Voltage	$v_{ m EBO}$	5	V
Collector Current	$I_{\mathbf{C}}$	50	mA
Base Current	I_{B}	5	mA
Collector Power Dissipation	PC	800	mA
Junction Temperature	T_{j}	150	°C
Storage Temperature Range	$ m T_{stg}$	-55~150	°C



Weight: 0.36g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	$V_{CB} = 150V, I_{E} = 0$	_		0.1	μ A
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_{C}=0$	_	I	0.1	μ A
Collector-Emitter Breakdown Voltage	V _(BR) CEO	$I_{C}=1$ mA, $I_{B}=0$	150	1	_	V
DC Current Gain	h _{FE} (Note)	$V_{\text{CE}} = 5V, I_{\text{C}} = 10\text{mA}$	80		240	
Collector-Emitter Saturation Voltage	V _{CE} (sat)	$I_C = 10 \text{mA}, I_B = 1 \text{mA}$	_		1.0	V
Base-Emitter Voltage	$V_{ m BE}$	$V_{\text{CE}} = 5V, I_{\text{C}} = 10\text{mA}$	_	_	0.8	V
Transition Frequency	f_{T}	$V_{\text{CE}} = 5V, I_{\text{C}} = 10\text{mA}$	_	200	_	MHz
Collector Output Capacitance	C_{ob}	$V_{CB} = 10V, I_{E} = 0, f = 1MHz$	_	1.8	_	pF

Note: hFE Classification $O:80 \sim 160$, $Y:120 \sim 240$

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